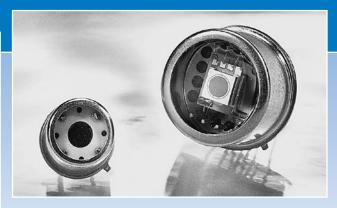
Dual Sandwich Detector Series

Two Color Photodiodes

Dual Sandwich Detectors or Two Color Detectors are mostly employed for remote temperature measurements. The temperature is measured by taking the ratio of radiation intensities of two adjacent wavelengths and comparing them with the standard black body radiation curves. The advantages of optical remote measurement have definitely made these devices the perfect match for this type of measurements. They are independent of emissivity and unaffected by contaminants in the field of view or moving targets. In addition, measurements of targets out of the direct line of sight and the ability to function from outside RF/EMI interference or vacuum areas are possible. They also have the advantages of overcoming obstructed target views, blockages from sight tubes, channels or screens, atmospheric smoke, steam, or dust, dirty windows as well as targets smaller than field of view and/or moving within the field of view. These detectors can also be used in applications where wide wavelength range of detection is needed.

OSI Optoelectronics offers three types of dual sandwich detectors. The Silicon- Silicon sandwich, in which one silicon photodiode is placed on top of the other, with the photons of shorter wavelengths absorbed in the top silicon and the photons of longer wavelengths penetrating deeper,



APPLICATIONS

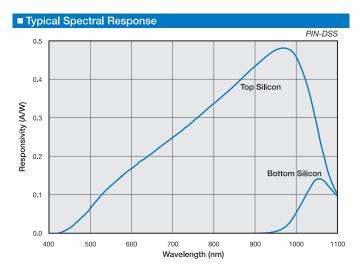
- Flame Temperature sensing
- Spectrophotometer
- Dual-wavelength detection
- IR Thermometers for Heat Treating, induction heating, and other metal parts processing

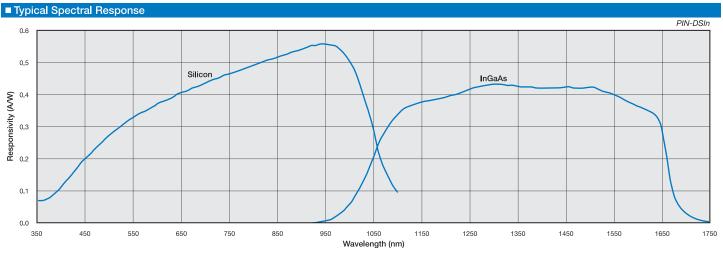
FEATURES

- Compact
- · Hermetically Sealed
- Low Noise
- Wide Wavelength Range
- Remote Measurements
- w/ TEC

absorbed by the bottom photodiode. For applications requiring a wider range of wavelength beyond 1.1 µm, an InGaAs photodiode replaces the bottom photodiode. The Silicon-InGaAs version is also available with a two stage thermo-electric cooler for more accurate measurements by stabilizing the temperature of the InGaAs detector.

All devices are designed for photovoltaic operation (no bias), however, they may be biased if needed, to the maximum reverse voltage specified. They are ideal for coupling to an operational amplifier in the current mode. For further details refer to the "Photodiode Characteristics" section of this catalog.





Model Number	Detector Element	Active Area	Spectral Range (nm)	Peak Wavelength	Responsivity	Capacitance		Shunt P Resistance		D* @ peak	Reverse Voltage	Rise Time (µs)	Rai	np* nge C)	-
		Dimension (mm)		nm	λ_P	0 V	-10 mV		0V, λ _P	0V , λ _P	v	0 V 50 Ω λ _P	Operating	Storage	PackageStyle ¶
					A/W	pF			(W/√Hz)	(cm√Hz/W)					
				typ.	typ.	typ.	min.	typ.	typ.	typ.	max.	typ.			
Non-Cooled															
PIN-DSS	Si (top)	2.54 ф	400-1100	950	0.45	70	50	500	1.3 e -14	1.7 e +13	5	10	-40 ~ +100	-55 ~ +125	17 / TO-5
	Si		950-1100	1060	0.12	,,	30		4.8 e -14	4.7 e +12		150			
PIN-DSIn	Si (top)	2.54 φ	400-1100	950	0.55 §	450	1	50	1.9 e -14 §	1.2 e +13 §	5	4			
	InGaAs	1.50 ф	1000-1800	1300	0.60	300	1	1.0	2.1 e -13	8.4 e +11	2	4	7		
Two Stage Thermoelectrically Cooled #															
PIN-DSIn-TEC	Si (top)	2.54 φ	400-1100	950	0.55 §	450	150		1.9 e -14 §	1.2 e +13 §	5	4	+100	+125	24 /
	InGaAs	1.5 φ	1000-1800	1300	0.60	300	1	1.0	2.1 e -13	8.4 e +11	2	4	~ 40 ~	-55 ~	TO-8

Thermistor Specifications

PARAMETER	CONDITION	SPECIFICATION			
Temperature Range		-100 °C to +100 °C			
Nominal Resistance		1.25 KW @ 25 °C			
	-100 °C to -25 °C	± 6.5 °C			
Accuracy	-25 °C to +50 °C	± 3.5 °C			
7.000.00	@ 25 °C	± 1.5 °C			
	+50 °C to +100 °C	± 6.7 °C			

Two Stage Thermo-electric Cooler Specifications

PARAMETER	SYMBOL	COND	ITION	SPECIFICATION		
Maximum Achievable Temperature Difference	∆T _{MAX} (°C)	$I = I_{MAX}$	Vacuum	91		
	THAX (5)	QC = 0	Dry N2	83		
Maximum Amount Of Heat Absorbed At The Cold Face	Q _{MAX} (W)	$I = I_{MAX}, \Delta T = 0$		0.92		
Input Current Resulting In Greatest ΔT_{MAX}	I _{MAX} (A)	-		1.4		
Voltage At △T _{MAX}	V _{MAX} (V)			2.0		

 $[\]$ @ 870 nm $\$ Thermo-Electric Cooler and Thermistor Specifications are specified in the tables below.

For mechanical drawings please refer to pages 58 thru 69.

* Non-Condensing temperature and Storage Range, Non-Condensing Environment.

1. Parameter Definitions:

- A = Distance from top of chip to top of glass.
- a = Photodiode Anode.
- B = Distance from top of glass to bottom of case.
- c = Photodiode Cathode
- (Note: cathode is common to case in metal package products unless otherwise noted).
- W = Window Diameter.
- F.O.V. = Filed of View (see definition below).
- 2. Dimensions are in inches (1 inch = 25.4 mm).
- 3. Pin diameters are 0.018 ± 0.002" unless otherwise specified.
- 4. Tolerances (unless otherwise noted)

General: 0.XX ±0.01"

0.XXX ±0.005"

Chip Centering: ±0.010" Dimension 'A': ±0.015"

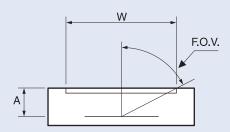
5. Windows

All '**UV**' Enhanced products are provided with QUARTZ glass windows, 0.027 ± 0.002 " thick.

All 'XUV' products are provided with removable windows.

All 'DLS' PSD products are provided with A/R coated glass windows.

All 'FIL' photoconductive and photovoltaic products are epoxy filled instead of glass windows.



$$F.O.V. = \tan^{-1} \left(\frac{W}{2A}\right)$$



For Further Assistance
Please Call One of Our Experienced
Sales and Applications Engineers

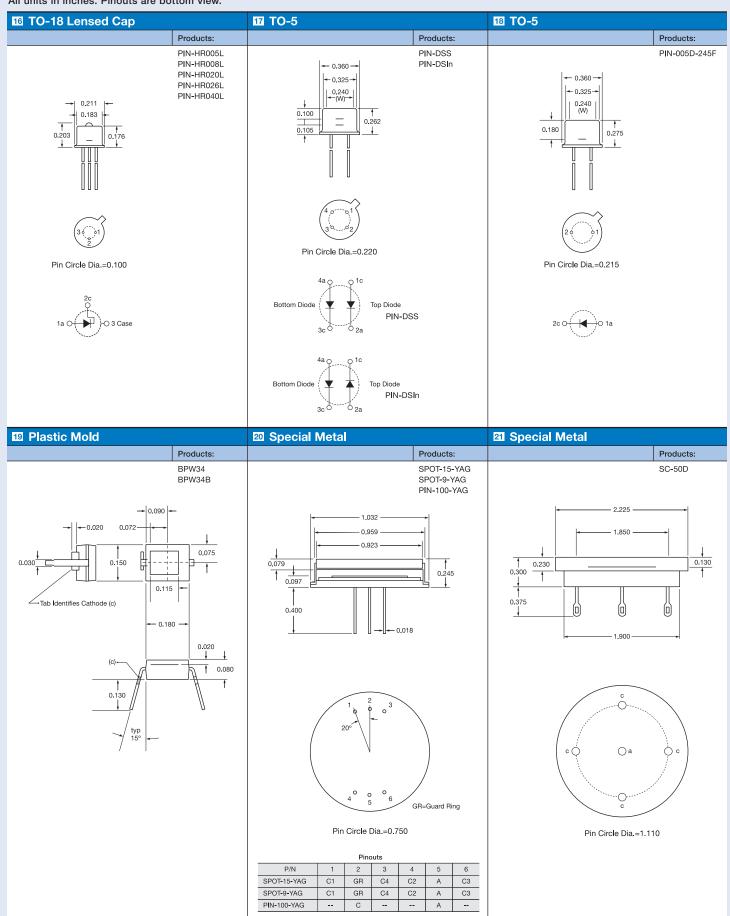
310-978-0516



On the Internet at www.osioptoelectronics.com

Mechanical Specifications

All units in inches. Pinouts are bottom view.



Mechanical Specifications

All units in inches. Pinouts are bottom view.

